



# PSMN028-100HS

N-channel 100 V, 27.5 mOhm, standard level MOSFET in LPAK56D using TrenchMOS technology

26 September 2022

Product data sheet

## 1. General description

Dual standard level N-channel MOSFET in an LPAK56D (Dual Power-SO8) package using TrenchMOS technology.

## 2. Features and benefits

- High peak drain current  $I_{DM}$
- Copper clip and flexible Leads
- High operating junction temperature  $T_j = 175\text{ °C}$
- Superior reliability
- Low body diode reverse recovery charge  $Q_r$

## 3. Applications

- Synchronous rectifier
- Forward and flyback converter
- Industrial drive
- Power management system
- Uninterruptible Power Supply (UPS)

## 4. Quick reference data

Table 1. Quick reference data

| Symbol                                       | Parameter                                    | Conditions                                                                                                                                                   | Min     | Typ  | Max  | Unit |
|----------------------------------------------|----------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------|---------|------|------|------|
| $V_{DS}$                                     | drain-source voltage                         | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                                                                                                   | -       | -    | 100  | V    |
| $I_D$                                        | drain current                                | $V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}; \text{Fig. 2}$                                                                                                 | -       | -    | 29   | A    |
| $P_{tot}$                                    | total power dissipation                      | $T_{mb} = 25\text{ °C}; \text{Fig. 1}$                                                                                                                       | -       | -    | 64   | W    |
| $T_j$                                        | junction temperature                         |                                                                                                                                                              | -55     | -    | 175  | °C   |
| <b>Static characteristics FET1 and FET2</b>  |                                              |                                                                                                                                                              |         |      |      |      |
| $R_{DS(on)}$                                 | drain-source on-state resistance             | $V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 25\text{ °C}; \text{Fig. 11}$                                                                                 | -       | 21.5 | 27.5 | mΩ   |
|                                              |                                              | $V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 175\text{ °C}; \text{Fig. 11}; \text{Fig. 12}$                                                                | -       | 55   | 76   | mΩ   |
| <b>Dynamic characteristics FET1 and FET2</b> |                                              |                                                                                                                                                              |         |      |      |      |
| $Q_{GD}$                                     | gate-drain charge                            | $I_D = 5\text{ A}; V_{DS} = 80\text{ V}; V_{GS} = 10\text{ V}; T_j = 25\text{ °C}; \text{Fig. 13}; \text{Fig. 14}$                                           | -       | 12.9 | -    | nC   |
| $Q_{G(tot)}$                                 | total gate charge                            |                                                                                                                                                              | -       | 34   | -    | nC   |
| <b>Avalanche Ruggedness FET1 and FET2</b>    |                                              |                                                                                                                                                              |         |      |      |      |
| $E_{DS(AL)S}$                                | non-repetitive drain-source avalanche energy | $I_D = 29\text{ A}; V_{sup} \leq 100\text{ V}; R_{GS} = 50\text{ }\Omega; V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C}; \text{unclamped}; \text{Fig. 4}$ | [1] [2] | -    | 67   | mJ   |

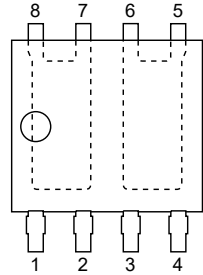
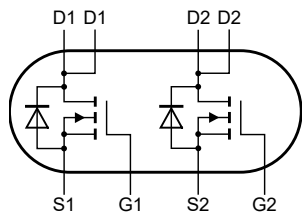
N-channel 100 V, 27.5 mOhm, standard level MOSFET in LPAK56D using TrenchMOS technology

| Symbol                                  | Parameter        | Conditions                                                                                                                   | Min | Typ  | Max | Unit |
|-----------------------------------------|------------------|------------------------------------------------------------------------------------------------------------------------------|-----|------|-----|------|
| <b>Source-drain diode FET1 and FET2</b> |                  |                                                                                                                              |     |      |     |      |
| Q <sub>r</sub>                          | recovered charge | I <sub>S</sub> = 5 A; di <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; T <sub>J</sub> = 25 °C | -   | 52.8 | -   | nC   |

- [1] Refer to application note AN10273 for further information
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline                                                                                                    | Graphic symbol                                                                                    |
|-----|--------|-------------|-----------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------|
| 1   | S1     | source1     |  <p>LPAK56D; Dual LPAK (SOT1205)</p> |  <p>mbk725</p> |
| 2   | G1     | gate1       |                                                                                                                       |                                                                                                   |
| 3   | S2     | source2     |                                                                                                                       |                                                                                                   |
| 4   | G2     | gate2       |                                                                                                                       |                                                                                                   |
| 5   | D2     | drain2      |                                                                                                                       |                                                                                                   |
| 6   | D2     | drain2      |                                                                                                                       |                                                                                                   |
| 7   | D1     | drain1      |                                                                                                                       |                                                                                                   |
| 8   | D1     | drain1      |                                                                                                                       |                                                                                                   |

## 6. Ordering information

Table 3. Ordering information

| Type number   | Package            |                                                                  | Version |
|---------------|--------------------|------------------------------------------------------------------|---------|
|               | Name               | Description                                                      |         |
| PSMN028-100HS | LPAK56D; Dual LPAK | plastic, single ended surface mounted package (LPAK56D); 8 leads | SOT1205 |

## 7. Marking

Table 4. Marking codes

| Type number   | Marking code |
|---------------|--------------|
| PSMN028-100HS | 28RS10H      |

## 8. Limiting values

Table 5. Limiting values

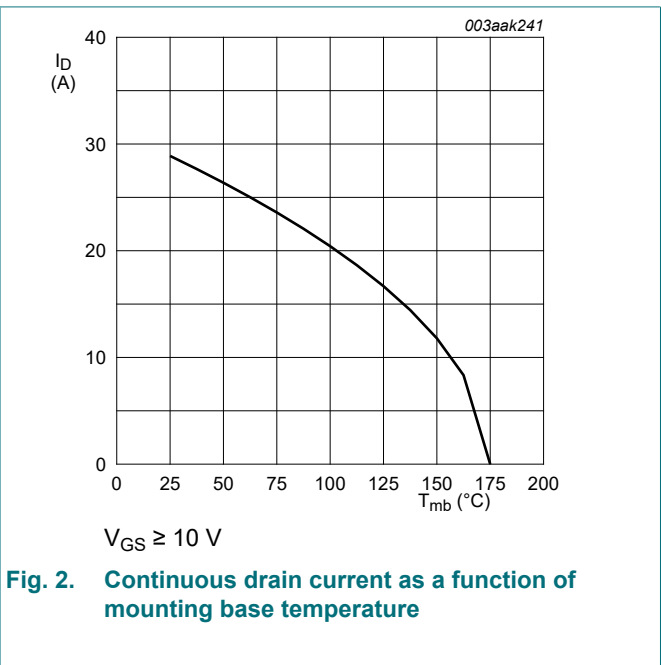
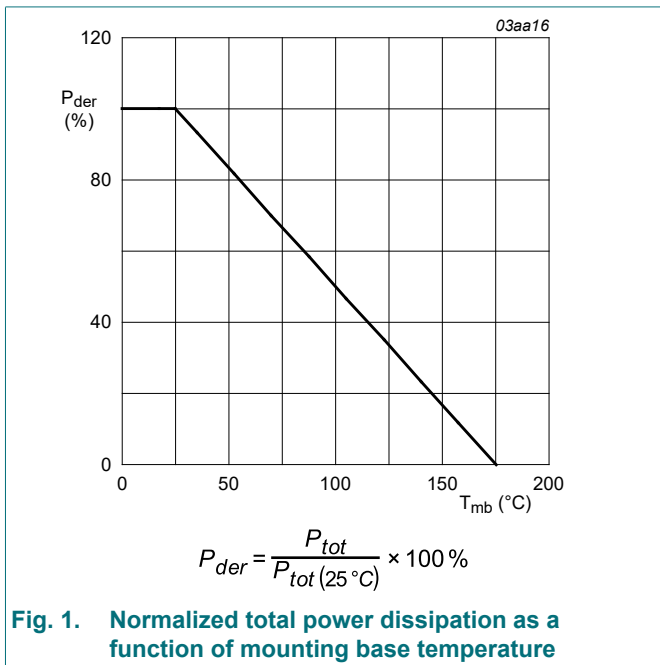
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions                                               | Min | Max  | Unit |
|------------------|-------------------------|----------------------------------------------------------|-----|------|------|
| V <sub>DS</sub>  | drain-source voltage    | 25 °C ≤ T <sub>J</sub> ≤ 175 °C                          | -   | 100  | V    |
| V <sub>DGR</sub> | drain-gate voltage      | R <sub>GS</sub> = 20 kΩ                                  | -   | 100  | V    |
| V <sub>GS</sub>  | gate-source voltage     | DC; T <sub>J</sub> ≤ 175 °C                              | -20 | 20   | V    |
| P <sub>tot</sub> | total power dissipation | T <sub>mb</sub> = 25 °C; Fig. 1                          | -   | 64   | W    |
| I <sub>D</sub>   | drain current           | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; Fig. 2  | -   | 29   | A    |
|                  |                         | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; Fig. 2 | -   | 20.4 | A    |

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| Symbol                                    | Parameter                                    | Conditions                                                                                                                                                                  | Min     | Max | Unit             |
|-------------------------------------------|----------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------|-----|------------------|
| $I_{DM}$                                  | peak drain current                           | pulsed; $t_p \leq 10 \mu\text{s}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$ ; Fig. 3                                                                                           | -       | 116 | A                |
| $T_{stg}$                                 | storage temperature                          |                                                                                                                                                                             | -55     | 175 | $^\circ\text{C}$ |
| $T_j$                                     | junction temperature                         |                                                                                                                                                                             | -55     | 175 | $^\circ\text{C}$ |
| $T_{sld(M)}$                              | peak soldering temperature                   |                                                                                                                                                                             | -       | 260 | $^\circ\text{C}$ |
| <b>Source-drain diode FET1 and FET2</b>   |                                              |                                                                                                                                                                             |         |     |                  |
| $I_S$                                     | source current                               | $T_{mb} = 25 \text{ }^\circ\text{C}$                                                                                                                                        | -       | 29  | A                |
| $I_{SM}$                                  | peak source current                          | pulsed; $t_p \leq 10 \mu\text{s}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$                                                                                                    | -       | 116 | A                |
| <b>Avalanche Ruggedness FET1 and FET2</b> |                                              |                                                                                                                                                                             |         |     |                  |
| $E_{DS(AL)S}$                             | non-repetitive drain-source avalanche energy | $I_D = 29 \text{ A}$ ; $V_{sup} \leq 100 \text{ V}$ ; $R_{GS} = 50 \Omega$ ; $V_{GS} = 10 \text{ V}$ ; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; unclamped; Fig. 4 | [1] [2] | -   | 67 mJ            |

- [1] Refer to application note AN10273 for further information
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175  $^\circ\text{C}$



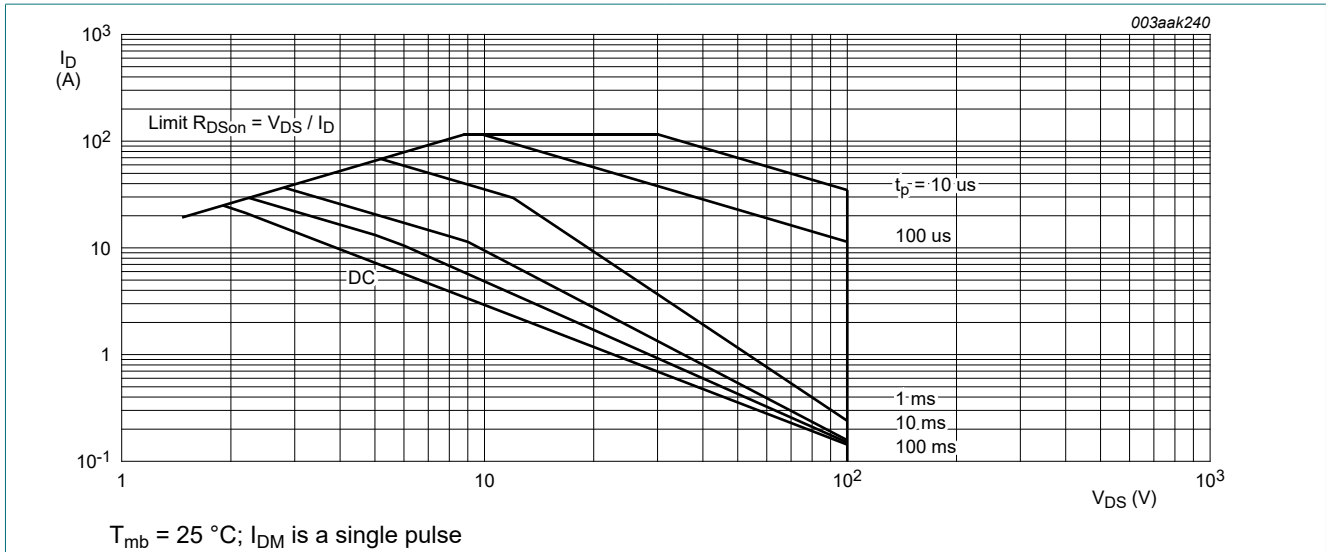


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

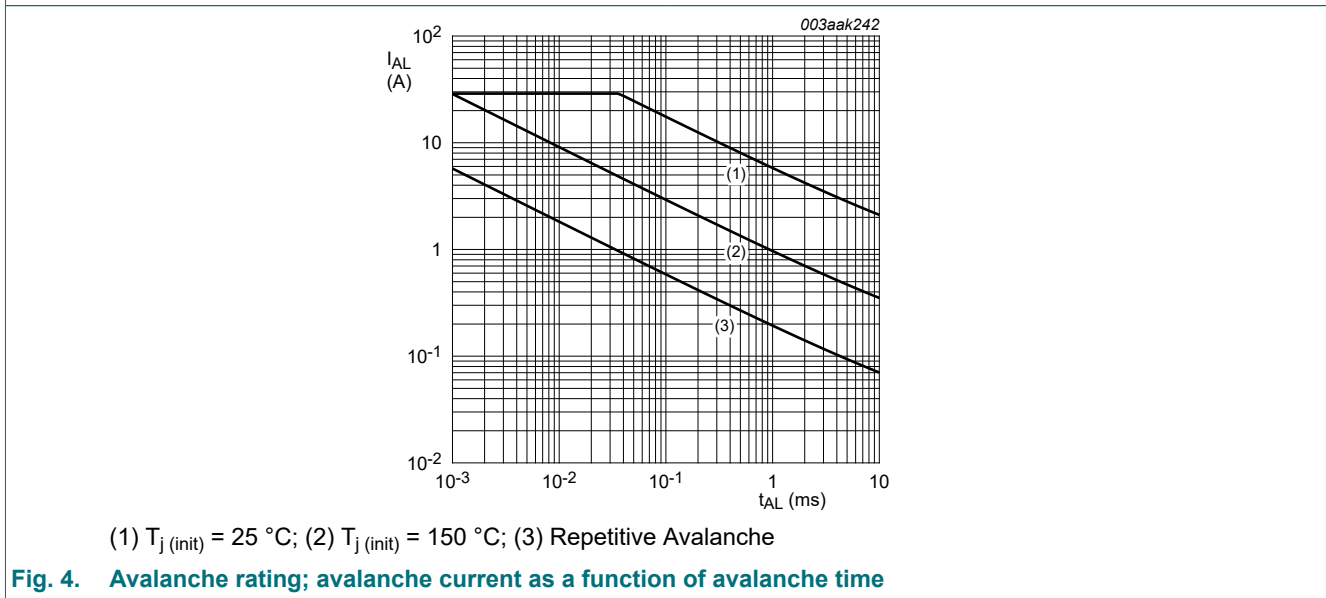


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                         | Conditions                                            | Min | Typ | Max  | Unit |
|----------------|---------------------------------------------------|-------------------------------------------------------|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5                                                | -   | -   | 2.36 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | Minimum footprint; mounted on a printed circuit board | -   | 95  | -    | K/W  |

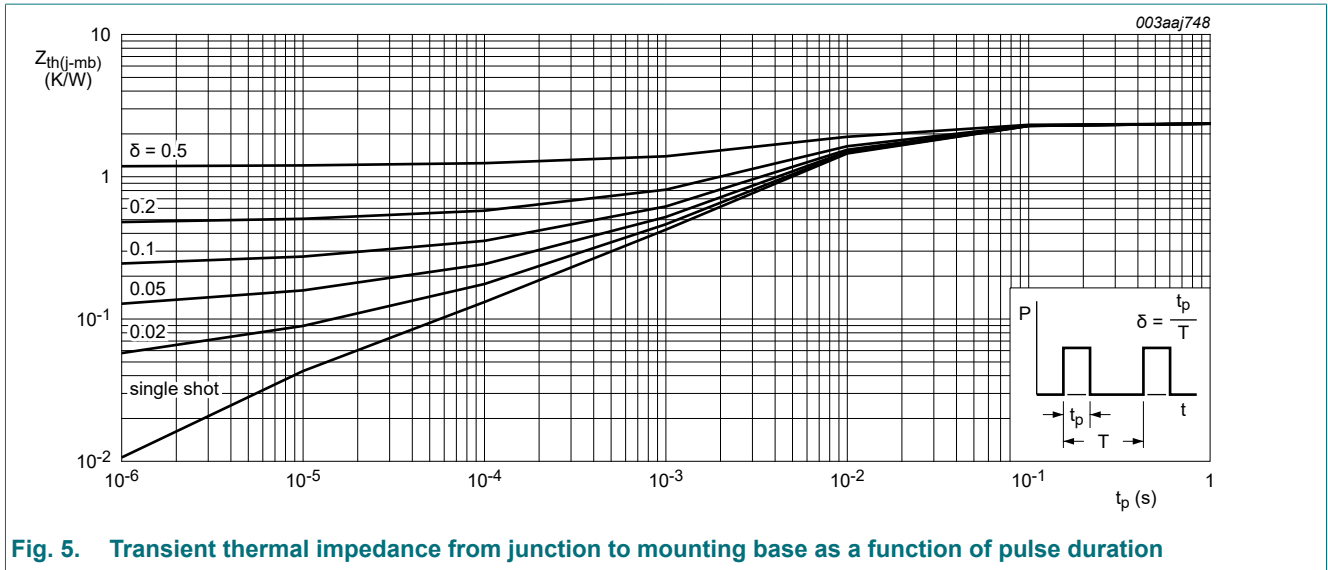


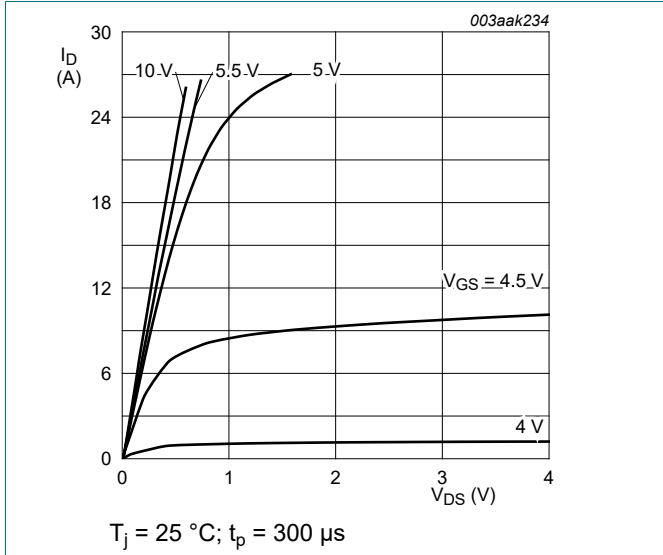
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

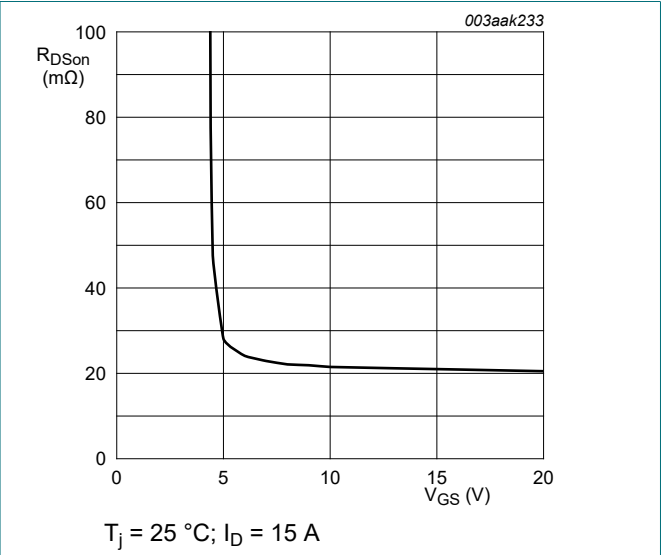
Table 7. Characteristics

| Symbol                                       | Parameter                        | Conditions                                                                                                                                       | Min | Typ  | Max  | Unit       |
|----------------------------------------------|----------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------|-----|------|------|------------|
| <b>Static characteristics FET1 and FET2</b>  |                                  |                                                                                                                                                  |     |      |      |            |
| $V_{(BR)DSS}$                                | drain-source breakdown voltage   | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$                                                                                      | 90  | -    | -    | V          |
|                                              |                                  | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$                                                                                       | 100 | -    | -    | V          |
| $V_{GS(th)}$                                 | gate-source threshold voltage    | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C$ ; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>                                | 2.4 | 3    | 4    | V          |
|                                              |                                  | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ }^\circ C$ ; <a href="#">Fig. 10</a>                                                        | 1   | -    | -    | V          |
|                                              |                                  | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ C$ ; <a href="#">Fig. 10</a>                                                        | -   | -    | 4.5  | V          |
| $I_{DSS}$                                    | drain leakage current            | $V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$                                                                        | -   | 0.02 | 1    | $\mu A$    |
|                                              |                                  | $V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ C$                                                                       | -   | -    | 500  | $\mu A$    |
| $I_{GSS}$                                    | gate leakage current             | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$                                                                        | -   | 2    | 100  | nA         |
|                                              |                                  | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$                                                                         | -   | 2    | 100  | nA         |
| $R_{DSon}$                                   | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ }^\circ C$ ; <a href="#">Fig. 11</a>                                                  | -   | 21.5 | 27.5 | m $\Omega$ |
|                                              |                                  | $V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 175 \text{ }^\circ C$ ; <a href="#">Fig. 11</a> ; <a href="#">Fig. 12</a>                       | -   | 55   | 76   | m $\Omega$ |
| <b>Dynamic characteristics FET1 and FET2</b> |                                  |                                                                                                                                                  |     |      |      |            |
| $Q_{G(tot)}$                                 | total gate charge                | $I_D = 5 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ }^\circ C$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> | -   | 34   | -    | nC         |
| $Q_{GS}$                                     | gate-source charge               |                                                                                                                                                  | -   | 6.5  | -    | nC         |
| $Q_{GD}$                                     | gate-drain charge                |                                                                                                                                                  | -   | 12.9 | -    | nC         |
| $C_{iss}$                                    | input capacitance                | $V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$ ; <a href="#">Fig. 15</a>                            | -   | 1603 | 2137 | pF         |
| $C_{oss}$                                    | output capacitance               |                                                                                                                                                  | -   | 164  | 196  | pF         |
| $C_{rss}$                                    | reverse transfer capacitance     |                                                                                                                                                  | -   | 109  | 150  | pF         |
| $t_{d(on)}$                                  | turn-on delay time               | $V_{DS} = 80 \text{ V}; R_L = 15 \text{ } \Omega; V_{GS} = 10 \text{ V}; R_{G(ext)} = 5 \text{ } \Omega; T_j = 25 \text{ }^\circ C$              | -   | 7.8  | -    | ns         |
| $t_r$                                        | rise time                        |                                                                                                                                                  | -   | 10.9 | -    | ns         |
| $t_{d(off)}$                                 | turn-off delay time              |                                                                                                                                                  | -   | 24.2 | -    | ns         |
| $t_f$                                        | fall time                        |                                                                                                                                                  | -   | 13.8 | -    | ns         |

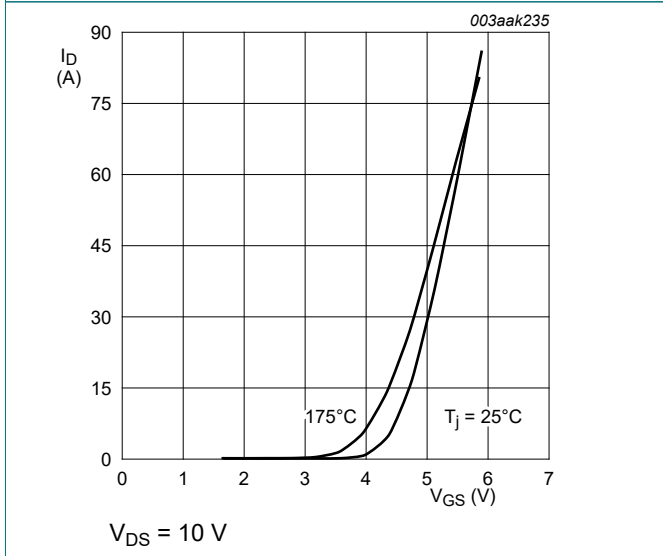
| Symbol                                  | Parameter             | Conditions                                                                              | Min | Typ  | Max | Unit |
|-----------------------------------------|-----------------------|-----------------------------------------------------------------------------------------|-----|------|-----|------|
| <b>Source-drain diode FET1 and FET2</b> |                       |                                                                                         |     |      |     |      |
| $V_{SD}$                                | source-drain voltage  | $I_S = 5\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; Fig. 16 | -   | 0.78 | 1.2 | V    |
| $t_{rr}$                                | reverse recovery time | $I_S = 5\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ;    | -   | 35.9 | -   | ns   |
| $Q_r$                                   | recovered charge      | $V_{DS} = 50\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$                               | -   | 52.8 | -   | nC   |



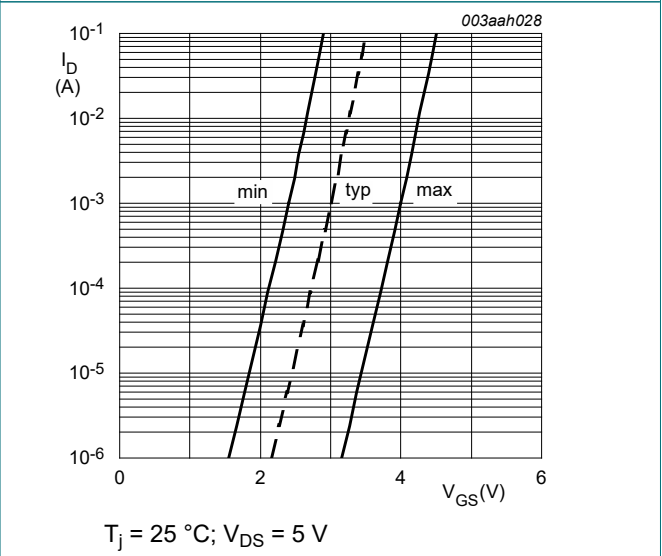
**Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values**



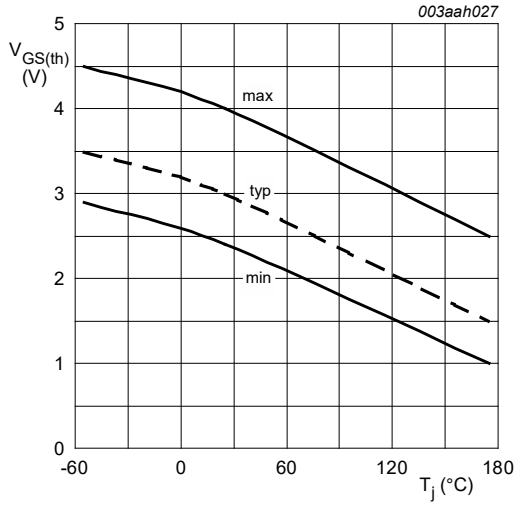
**Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values**



**Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values**

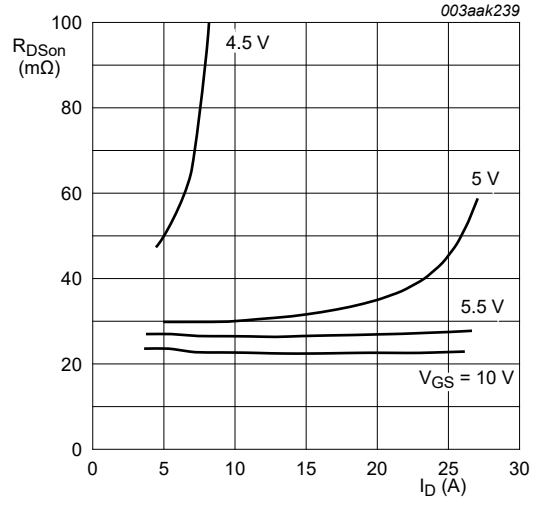


**Fig. 9. Sub-threshold drain current as a function of gate-source voltage**



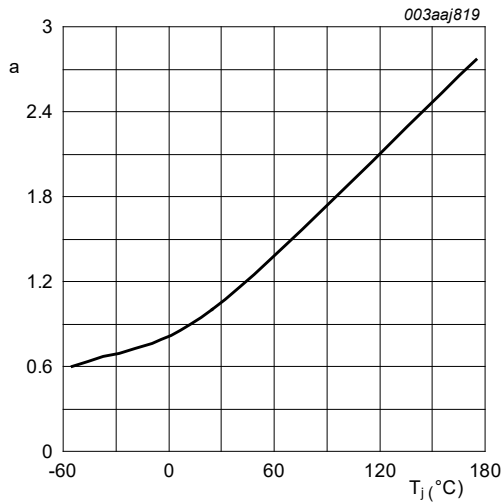
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

**Fig. 10. Gate-source threshold voltage as a function of junction temperature**



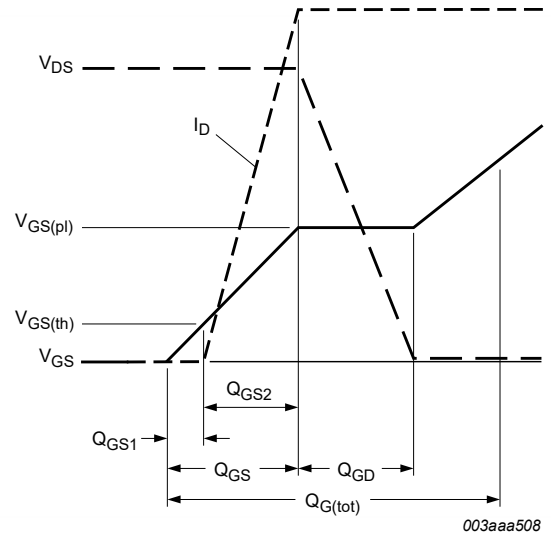
$T_j = 25 \text{ °C}; t_p = 300 \text{ μs}$

**Fig. 11. Drain-source on-state resistance as a function of drain current; typical values**



$$a = \frac{R_{DS(on)}}{R_{DS(on)}(25^\circ\text{C})}$$

**Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature**



**Fig. 13. Gate charge waveform definitions**

N-channel 100 V, 27.5 mOhm, standard level MOSFET in LPAK56D using TrenchMOS technology

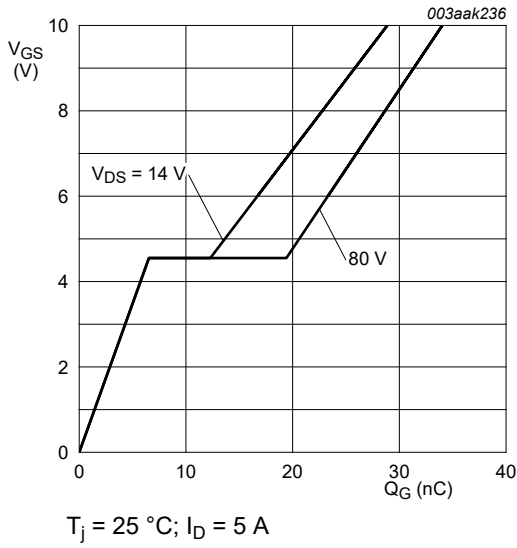


Fig. 14. Gate-source voltage as a function of gate charge; typical values

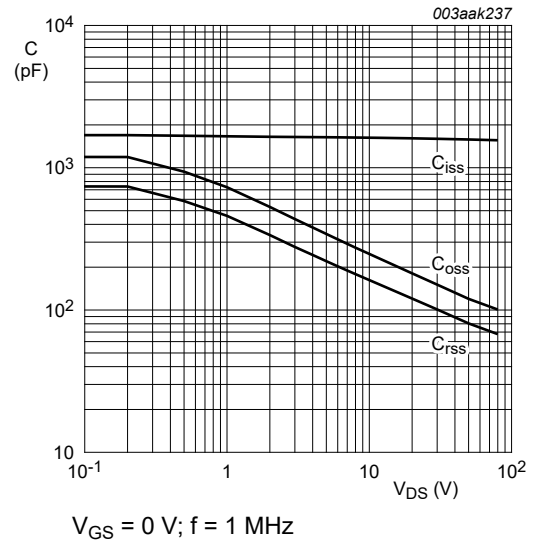


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

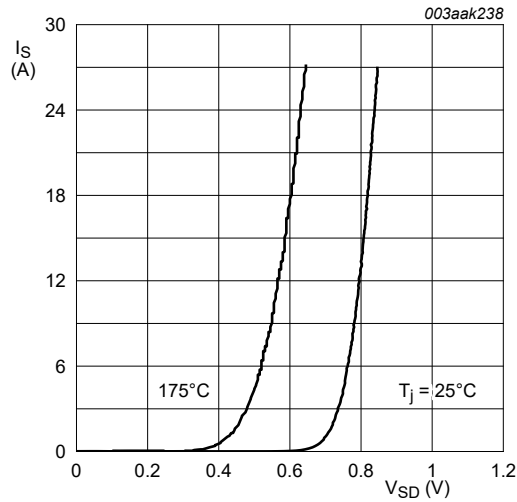


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values



### 11. Package outline

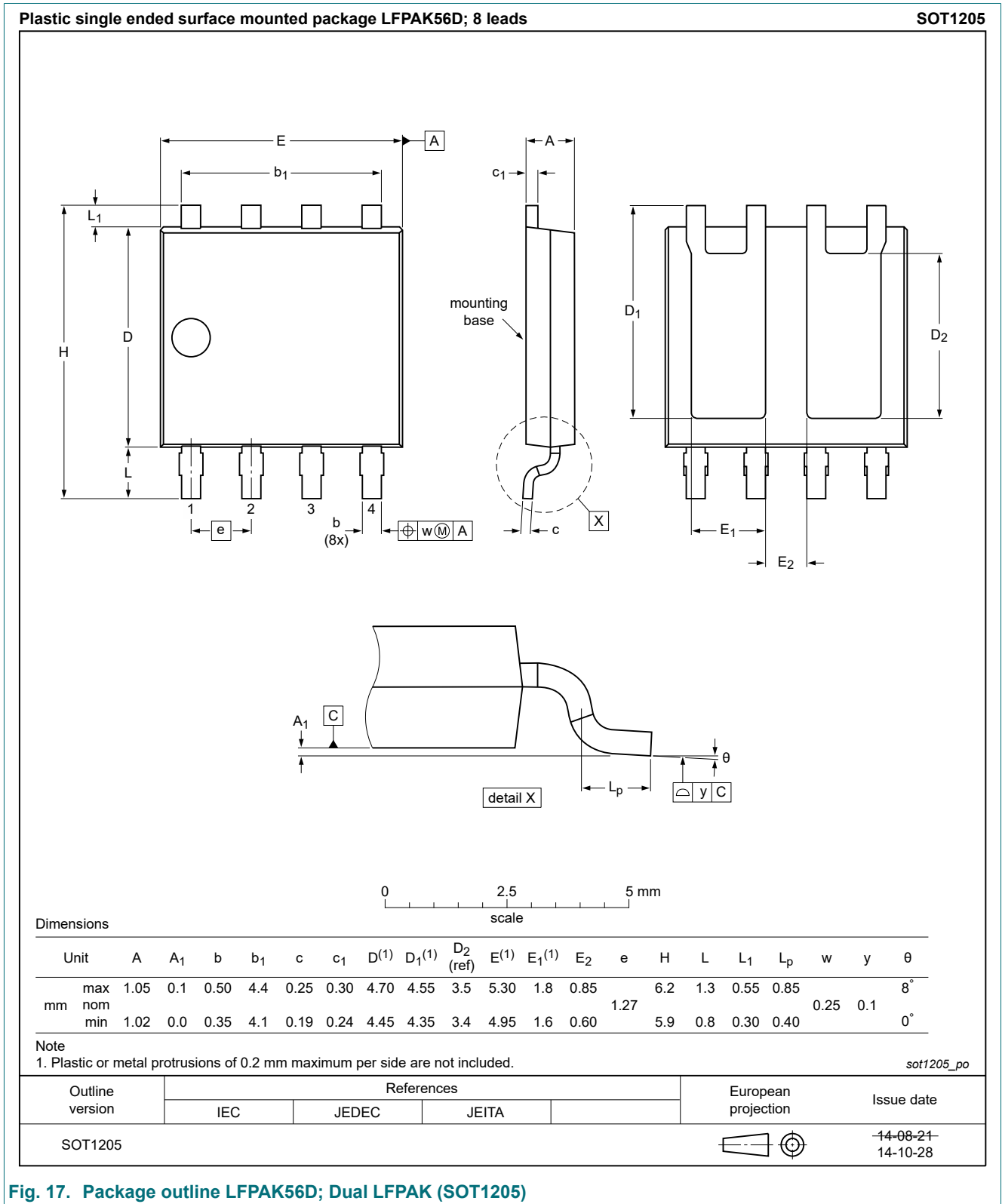


Fig. 17. Package outline LPAK56D; Dual LPAK (SOT1205)

## 12. Soldering

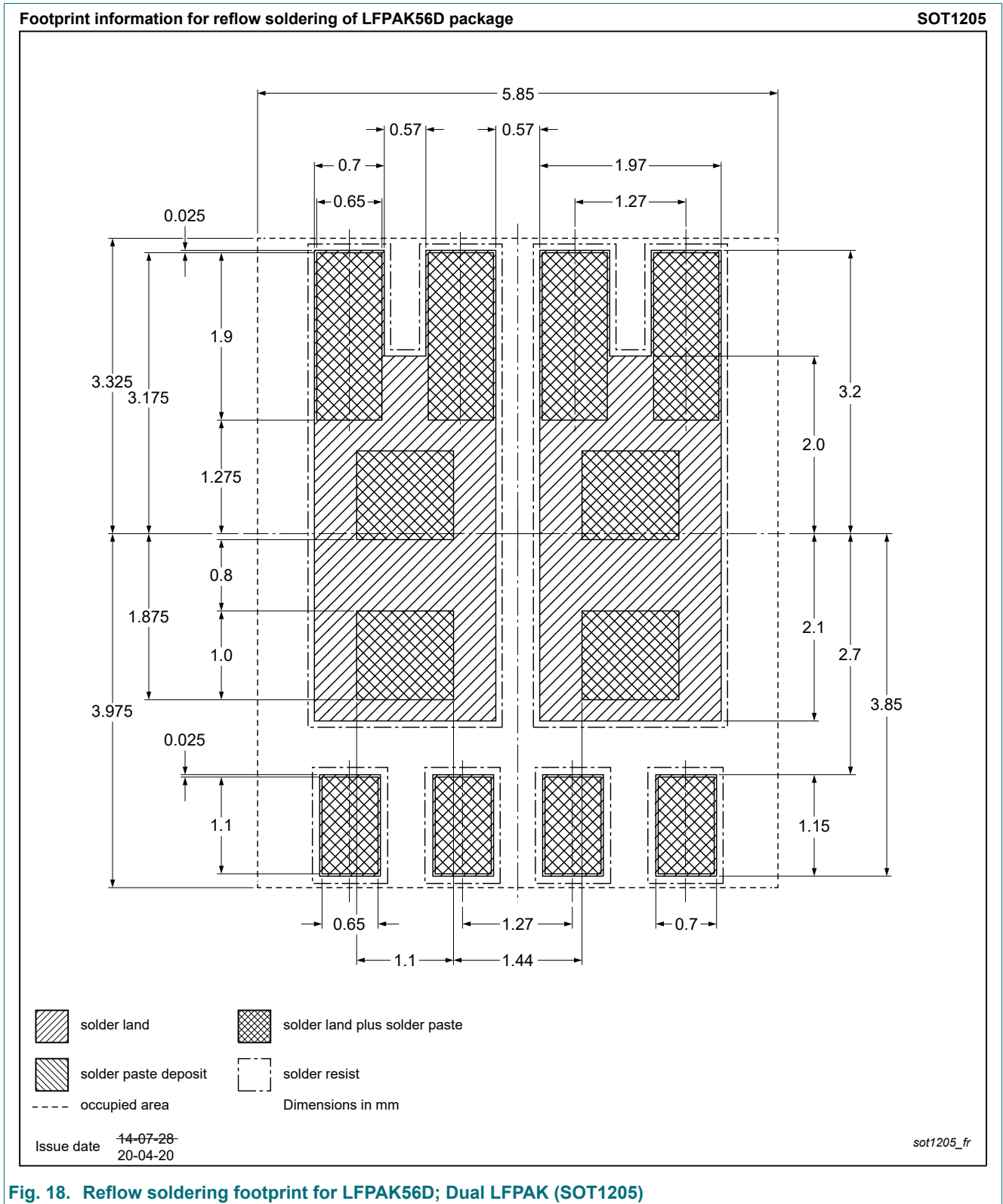


Fig. 18. Reflow soldering footprint for LPAK56D; Dual LPAK (SOT1205)

## 13. Legal information

### Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <https://www.nexperia.com>.

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